

Power MOSFET Demonstrates High Efficiency

Published on Wireless Design & Development (<http://www.wirelessdesignmag.com>)

Power MOSFET Demonstrates High Efficiency



Renesas Technology's RJK0383DPA dual-type power MOSFET achieves an efficiency rating of 91.6% in a synchronous-rectification circuit converting a 12 V DC input to a 1.1 V DC output at 600 kHz switching frequencies. The $5.3 \times 6.2 \times 0.8$ mm WPAK³-packaged device integrates high-side and low-side power MOSFETs and a Schottky barrier diode in DC/DC converters for laptop PCs and communication devices. The MOSFET exhibits a drain-gate load (Qgd) of 1.5 nC at a VDD of 10 V and a typical on-resistance of 3.7 m Ω at 4.5 V.

www.renesas.com
408-382-7500

Source URL (retrieved on 01/28/2015 - 11:25am):

http://www.wirelessdesignmag.com/product-releases/2008/08/power-mosfet-demonstrates-high-efficiency?qt-digital_editions=0